AMENDMENTS TO THE CLAIMS

Please amend the claims as follows:

1-30. (withdrawn)

31. (currently amended) A method of fabricating a device, comprising:

depositing an inorganic conductive or semiconductive layer disposed in an island configuration over a substrate, the substrate having an original configuration;

depositing an organic layer on the inorganic conductive or semiconductive layer, such that the organic layer is in direct physical contact with the inorganic conductive or semiconductive layer;

deforming the substrate such that there is an average radial or biaxial strain of at least 0.05% relative to the original configuration.

32. (original) The method of claim 31, wherein the substrate is deformed such that there is an average radial or biaxial strain of at least 1.5% relative to the original configuration.

33. (original) The method of claim 32, wherein the original configuration is a flat substrate.

34. (original) The method of claim 31, wherein the substrate is plastically deformed.

35. (original) The method of claim 31, wherein the substrate has a glass transition temperature, and the substrate is deformed at a temperature that exceeds its glass transition temperature.

36. (original) The method of claim 31, wherein the substrate is deformed at a maximum strain rate of 1.5% per 50 minutes.

37. (currently amended) A device fabricated by the process of:

depositing an inorganic conductive or semiconductive layer disposed in an island configuration over a substrate, the substrate having an original configuration;